

**Erratum: "Substrate orientation effects on dopant incorporation  
in InP grown by metalorganic chemical vapor deposition"  
[J. Appl. Phys. 73, 4095 (1993)]**

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The  $\langle 311 \rangle$ B InP substrates were mislabeled. They were actually  $\langle 311 \rangle$ A InP substrates.

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